



PJM05P40SA

P-Channel Enhancement Mode Power MOSFET

Product Summary

- $V_{DS} = -40V, I_D = -5A$
- $R_{DS(on)} < 88m\Omega @ V_{GS} = -10V$
- $R_{DS(on)} < 117m\Omega @ V_{GS} = -4.5V$

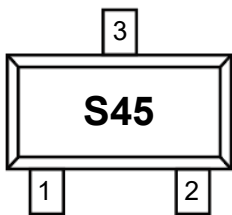
Features

- Advanced Trench Technology
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 1

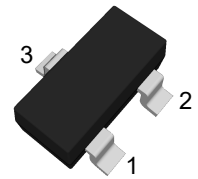
Application

- Load Switch
- PWM Application
- Power Management

Marking Code



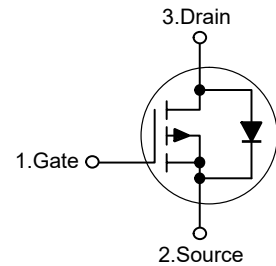
SOT-23



(Top View)

Pin	Description
1	Gate
2	Source
3	Drain

Schematic Diagram



Absolute Maximum Ratings

($T_a = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	$-I_D$	5	A
Drain Current-Pulsed ^{Note1}	$-I_{DM}$	20	A
Maximum Power Dissipation	P_D	1.2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ C$

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	104	$^\circ C/W$
--	-----------------	-----	--------------



PJM05P40SA

P-Channel Enhancement Mode Power MOSFET

Electrical Characteristics

(T_J=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	-V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	40	--	--	V
Zero Gate Voltage Drain Current	-I _{DSS}	V _{DS} =-40V, V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage ^{Note3}	-V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	1	1.6	2.5	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =-10V, I _D =-3A	--	68	88	mΩ
		V _{GS} =-4.5V, I _D =-2A	--	85	117	mΩ
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =-5V, I _D =-1A	--	4.5	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0V, f=1MHz	--	515	--	pF
Output Capacitance	C _{oss}		--	48	--	pF
Reverse Transfer Capacitance	C _{rss}		--	40	--	pF
Gate Resistance	R _G	V _{DS} =0V, V _{GS} =0V, f=1MHz	--	10.8	--	Ω
Total Gate Charge	Q _g	V _{DS} =-20V, I _D =-3A, V _{GS} =-10V	--	10	--	nC
Gate-Source Charge	Q _{gs}		--	2	--	nC
Gate-Drain Charge	Q _{gd}		--	1.6	--	nC
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-20V, I _D =-5A, V _{GS} =-10V, R _{GEN} =2.4Ω	--	7	--	nS
Turn-on Rise Time	t _r		--	19	--	nS
Turn-off Delay Time	t _{d(off)}		--	16	--	nS
Turn-off Fall Time	t _f		--	24	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	-V _{SD}	V _{GS} =0V, I _S =-5A	--	--	1.2	V
Diode Forward Current ^{Note2}	-I _S		--	--	5	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

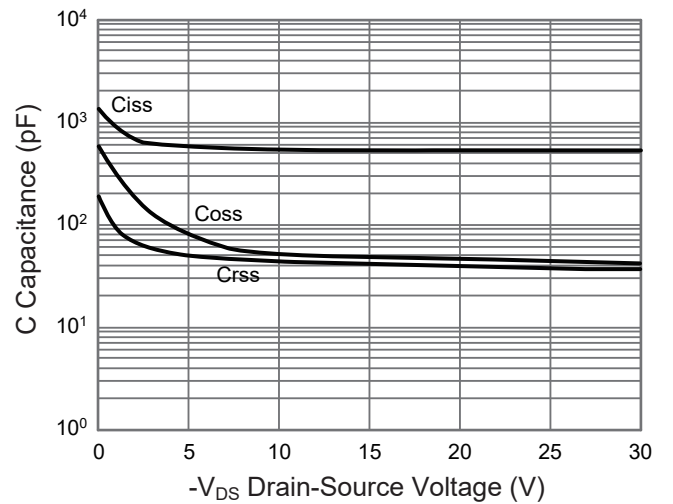
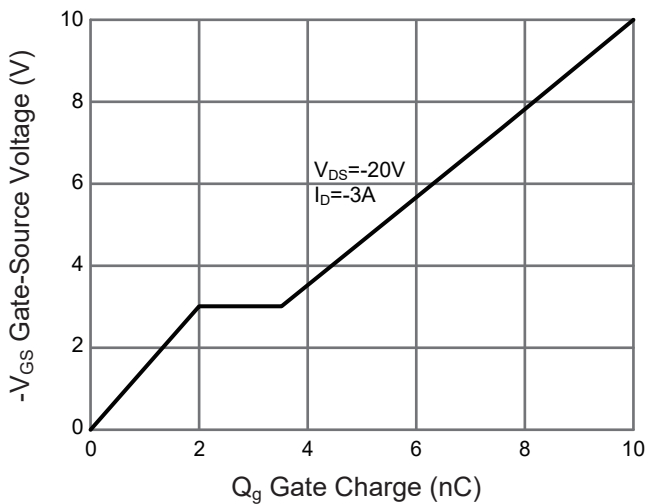
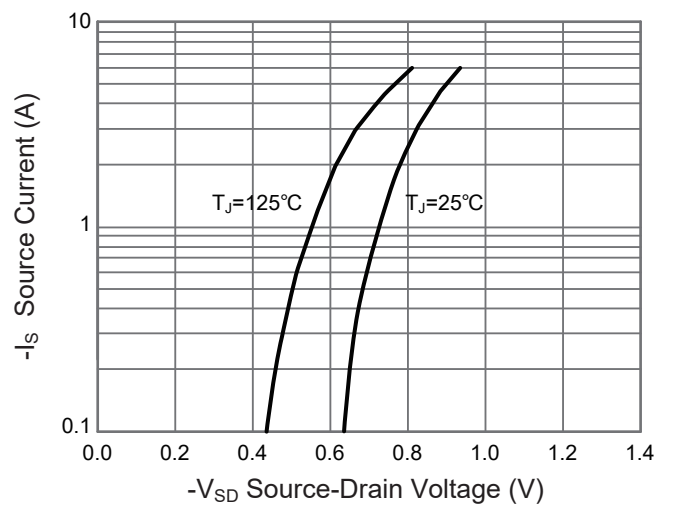
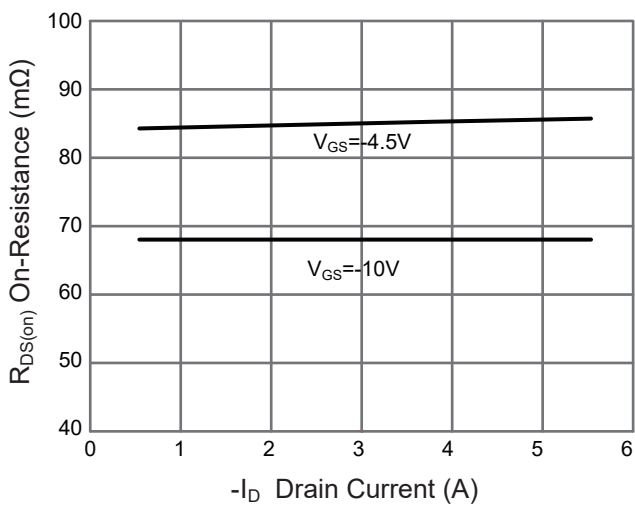
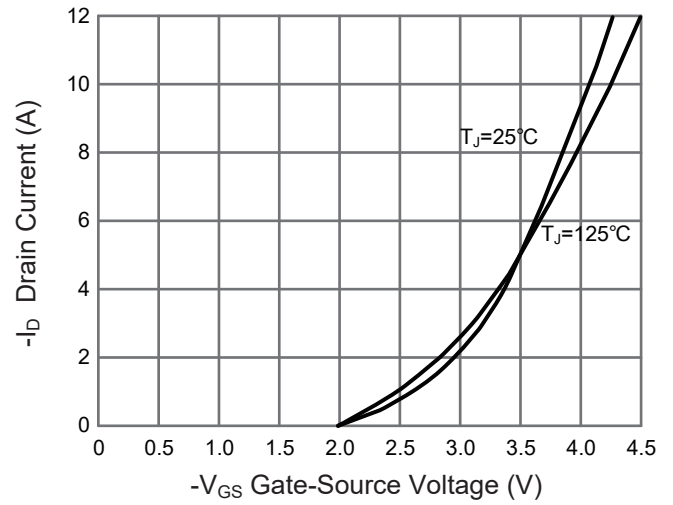
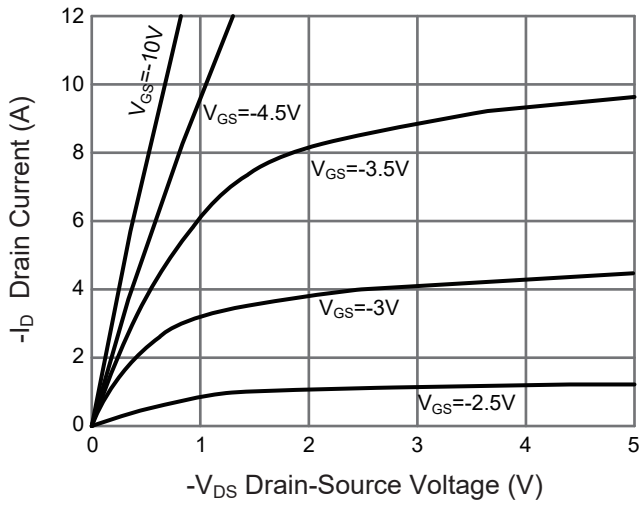
3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%.



PJM05P40SA

P-Channel Enhancement Mode Power MOSFET

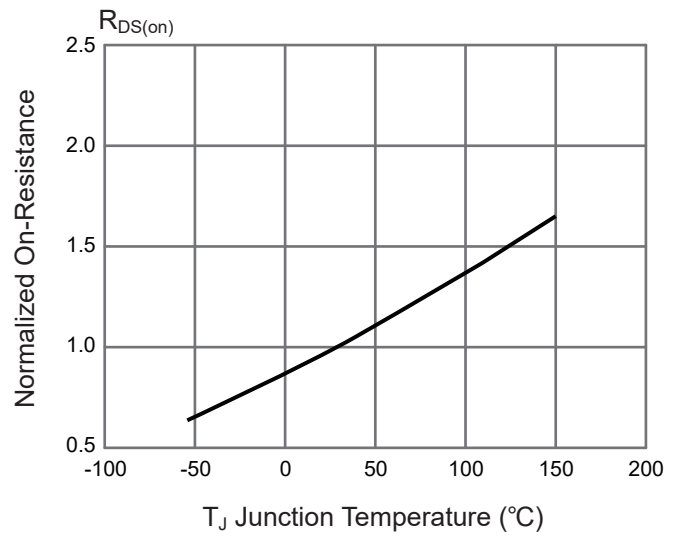
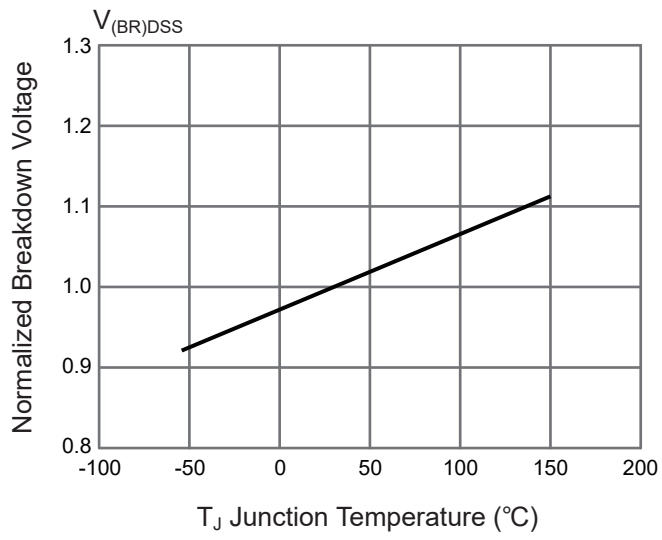
Typical Characteristic Curves





PJM05P40SA

P-Channel Enhancement Mode Power MOSFET





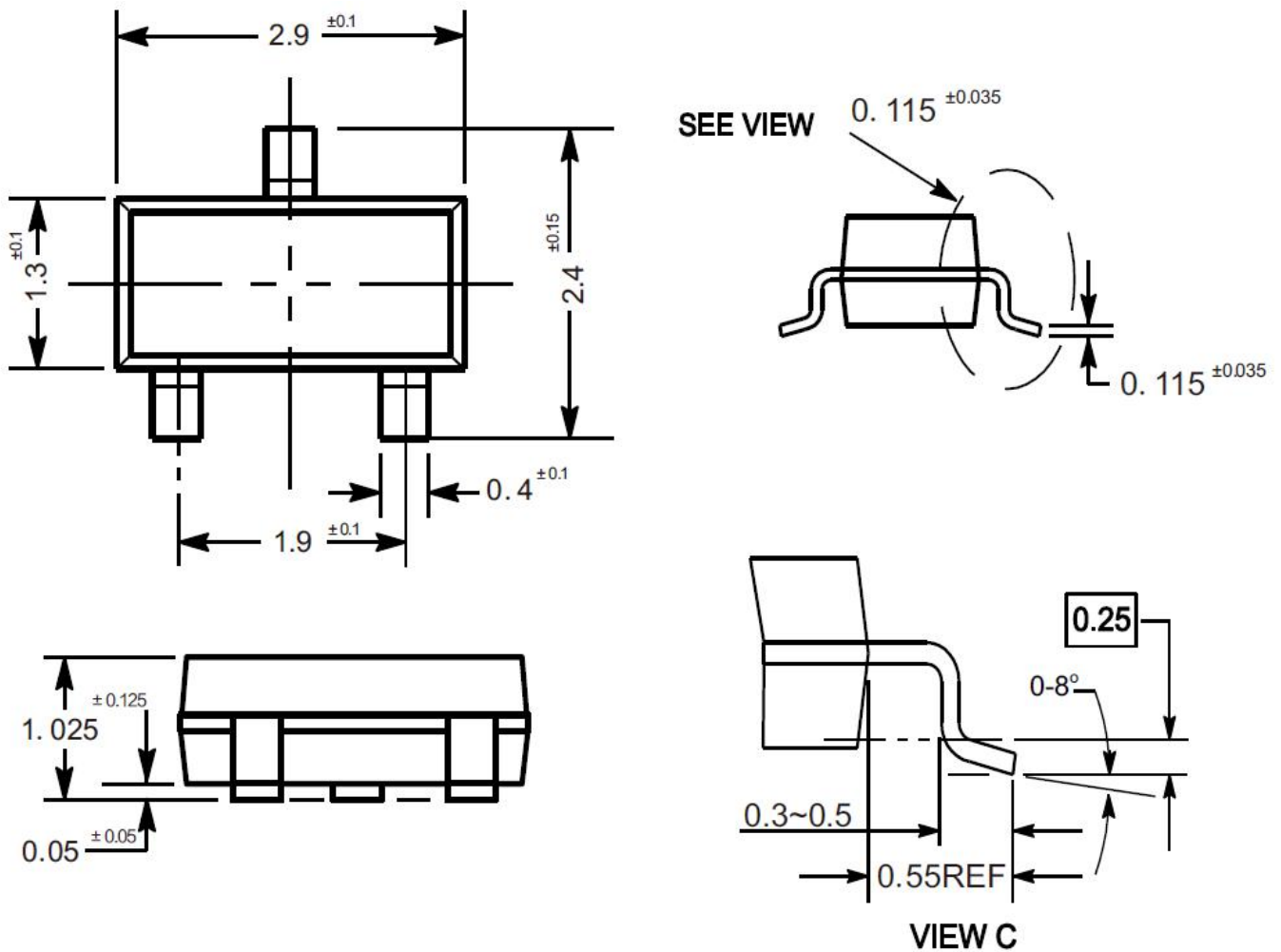
PJM05P40SA

P-Channel Enhancement Mode Power MOSFET

Package Outline

SOT-23

Dimensions in mm



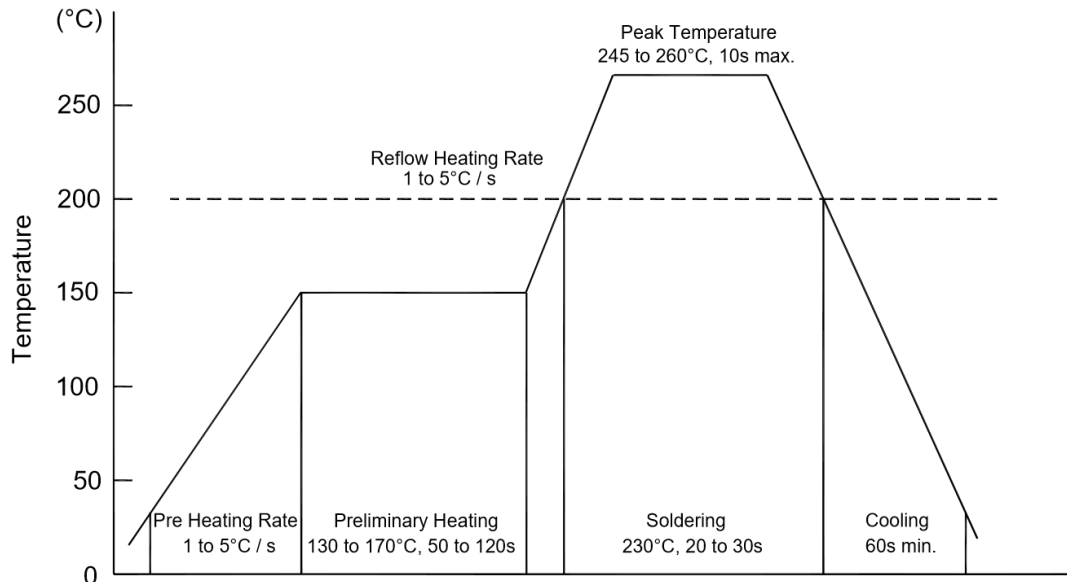
Ordering Information

Device	Package	Shipping
PJM05P40SA	SOT-23	3,000PCS/Reel&7inches



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

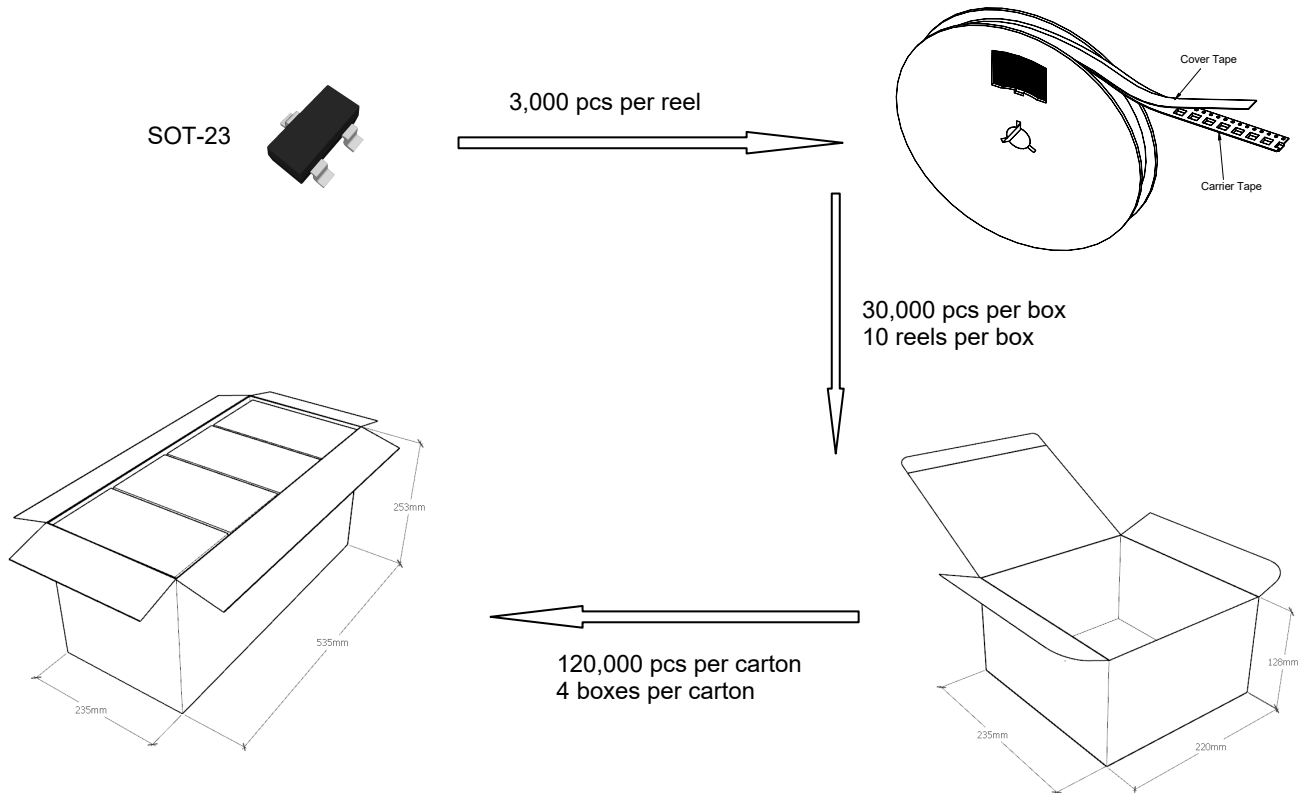
- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing



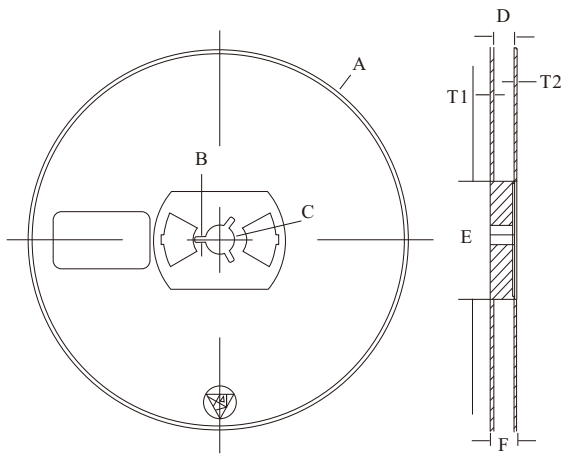
PJM05P40SA P-Channel Enhancement Mode Power MOSFET

Package Specifications

- The method of packaging

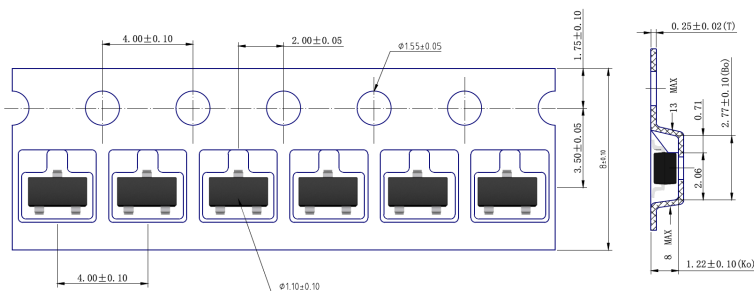


◆ Embossed tape and reel data



Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2

Reel (7")



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Pingjingsemi](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [2SK2267\(Q\)](#) [BUK455-60A/B](#) [TK100A10N1,S4X\(S](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#)
[IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [TK31J60W5,S1VQ\(O](#) [TK31J60W,S1VQ\(O](#) [TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#)
[DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)
[DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)
[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1_T0_00201](#) [PJMF380N65E1_T0_00201](#)
[PJMF280N60E1_T0_00201](#) [PJMF600N65E1_T0_00201](#) [PJMF900N65E1_T0_00201](#)